

HiPerFET™

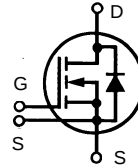
Power MOSFETs

Single Die MOSFET

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

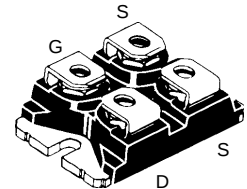
IXFN 36N100

$V_{DSS} = 1000V$
 $I_{D25} = 36A$
 $R_{DS(on)} = 0.24\Omega$



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$, Chip capability	36	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	144	A
I_{AR}	$T_C = 25^\circ C$	36	A
E_{AR}	$T_C = 25^\circ C$	64	mJ
E_{AS}	$T_C = 25^\circ C$	4	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ C$	700	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
V_{ISOL}	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500 3000	V~ V~
M_d	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source

D = Drain
TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- miniBLOC, with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

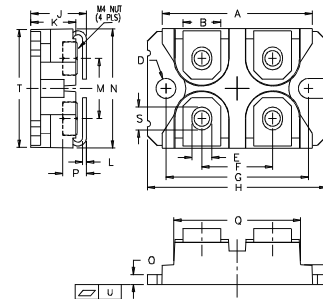
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ C$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 V$, $I_D = 3$ mA	1000		V
$V_{GH(th)}$	$V_{DS} = V_{GS}$, $I_D = 8$ mA	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}$, $V_{DS} = 0$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $T_J = 25^\circ C$ $V_{GS} = 0 V$, $T_J = 125^\circ C$			100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2\%$			0.24 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 15\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	18	40	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$			9200 pF
C_{oss}				1200 pF
C_{rss}				300 pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),			41 ns
t_r				55 ns
$t_{d(off)}$				110 ns
t_f				30 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$			380 nC
Q_{gs}				65 nC
Q_{gd}				185 nC
R_{thJC}				0.18 K/W
R_{thCK}				0.05 K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			36 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			144 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.3 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}, T_J = 25^\circ\text{C}$	180		ns
	$T_J = 125^\circ\text{C}$	330		ns
Q_{RM}	$T_J = 25^\circ\text{C}$	2		μC
I_{RM}		8		A

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025

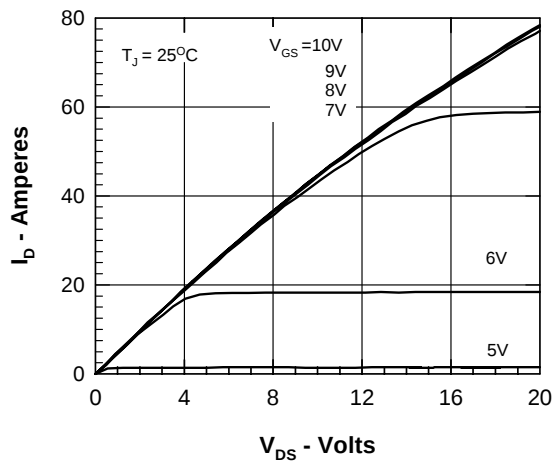


Figure 1. Output Characteristics at 25°C

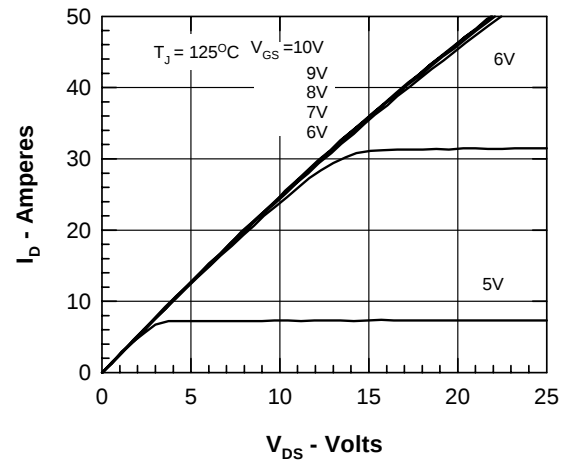


Figure 2. Output Characteristics at 125°C

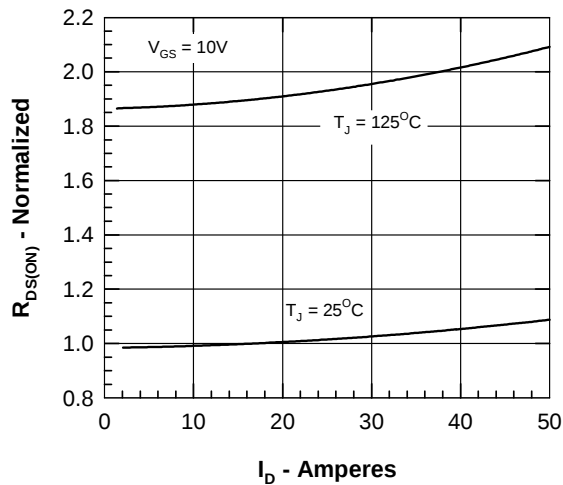


Figure 3. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value vs. I_D

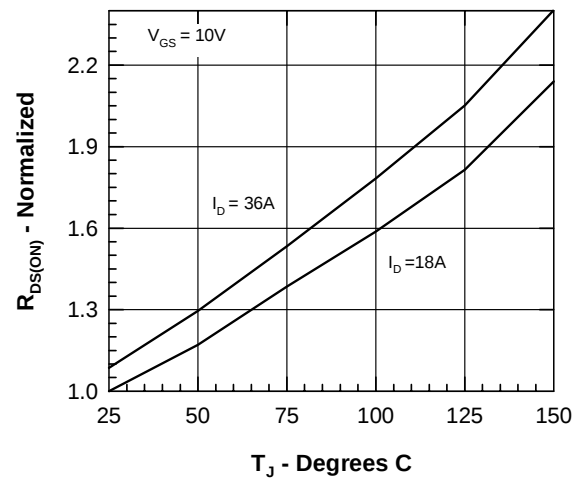


Figure 4. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value vs. T_J

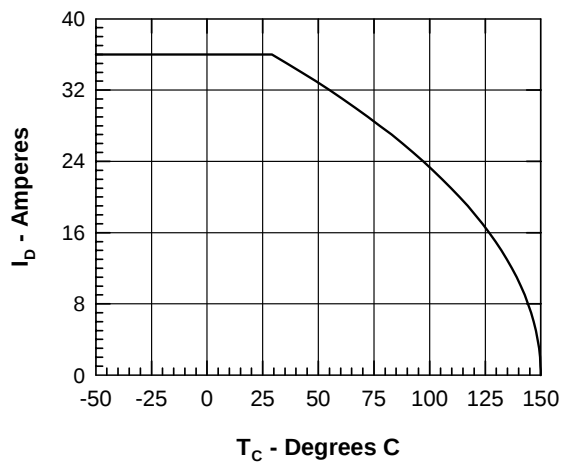


Figure 5. Drain Current vs. Case Temperature

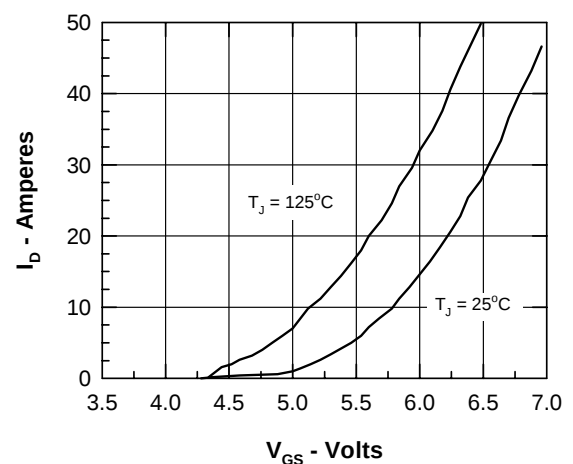


Figure 6. Admittance Curves

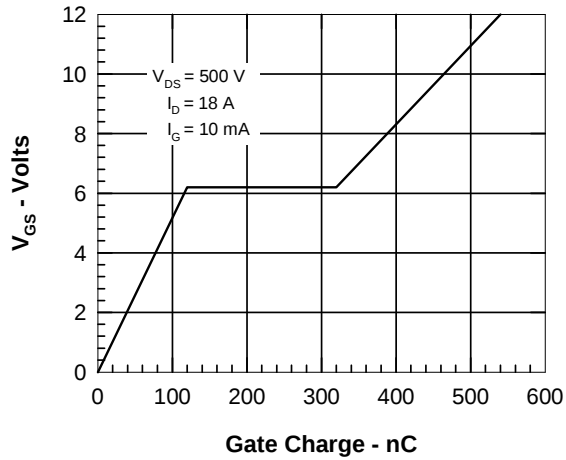


Figure 7. Gate Charge

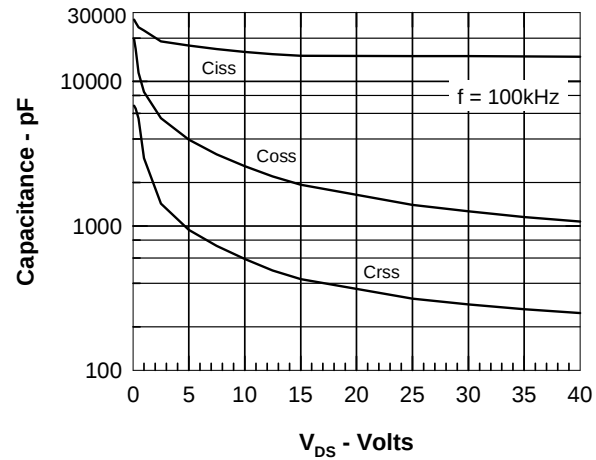


Figure 8. Capacitance Curves

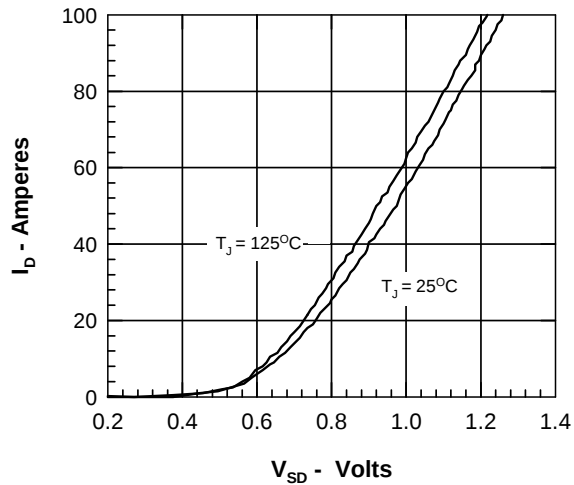


Figure 9. Forward Voltage Drop of the Intrinsic Diode

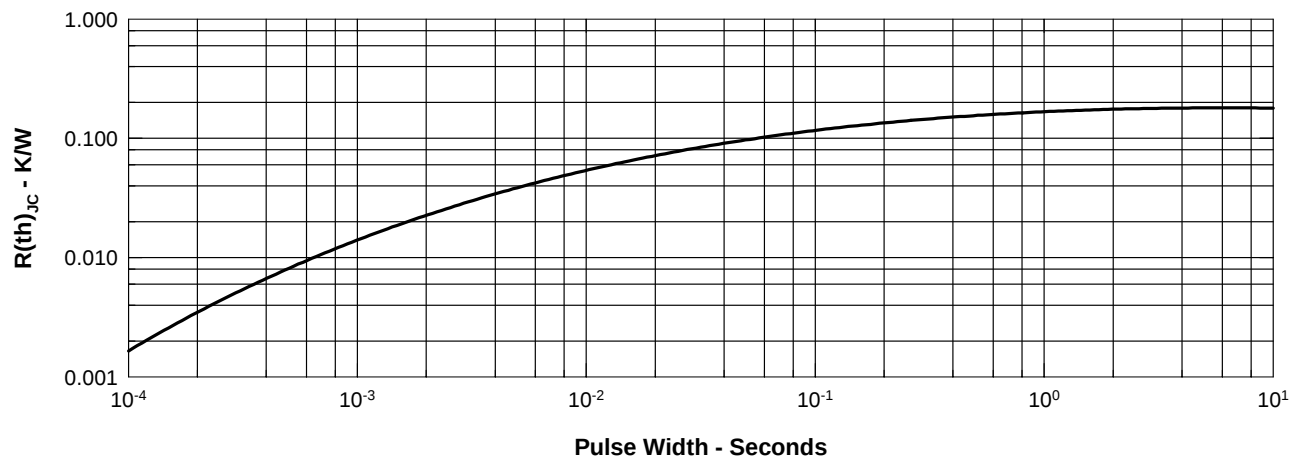


Figure 10. Transient Thermal Resistance

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